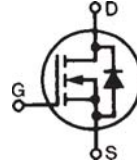


## Depletion Mode MOSFET

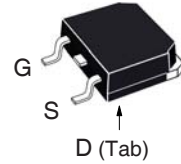
### IXTT2N170D2 IXTH2N170D2

$V_{DSX} = 1700V$   
 $I_{D(on)} \geq 2A$   
 $R_{DS(on)} \leq 6.5\Omega$

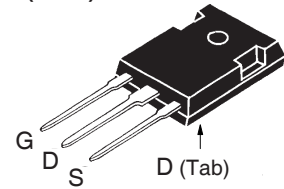
N-Channel



TO-268 (IXTT)



TO-247 (IXTH)



G = Gate      D = Drain  
 S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSX}$	$T_J = 25^\circ C$ to $150^\circ C$	1700	V
$V_{DGX}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	1700	V
$V_{GSX}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$P_D$	$T_C = 25^\circ C$	568	W
$T_J$		- 55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		- 55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-268	4	g
	TO-247	6	g

### Features

- Normally ON Mode
- International Standard Packages
- Molding Epoxies Meet UL 94 V-0 Flammability Classification

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- Audio Amplifiers
- Start-Up Circuits
- Protection Circuits
- Ramp Generators
- Current Regulators
- Active Loads

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSX}$	$V_{GS} = -5V$ , $I_D = 250\mu A$	1700		V
$V_{GS(off)}$	$V_{DS} = 25V$ , $I_D = 250\mu A$	- 2.5		- 4.5 V
$I_{GSX}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSX(off)}$	$V_{DS} = V_{DSX}$ , $V_{GS} = -5V$ $T_J = 125^\circ C$			25 $\mu A$ 500 $\mu A$
$R_{DS(on)}$	$V_{GS} = 0V$ , $I_D = 1A$ , Note 1			6.5 $\Omega$
$I_{D(on)}$	$V_{GS} = 0V$ , $V_{DS} = 50V$ , Note 1	2		A

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 30\text{V}, I_D = 1\text{A}$ , Note 1	1.4	2.2	S
$C_{iss}$	$V_{GS} = -10\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		3650	pF
$C_{oss}$			206	pF
$C_{rss}$			80	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = \pm 5\text{V}, V_{DS} = 850\text{V}, I_D = 1\text{A}$ $R_G = 2\Omega$ (External)		28	ns
$t_r$			58	ns
$t_{d(off)}$			33	ns
$t_f$			106	ns
$Q_{g(on)}$	$V_{GS} = \pm 5\text{V}, V_{DS} = 850\text{V}, I_D = 1\text{A}$		110	nC
$Q_{gs}$			12	nC
$Q_{gd}$			60	nC
$R_{thJC}$	TO-247			0.22 $^\circ\text{C/W}$
$R_{thCS}$			0.21	$^\circ\text{C/W}$

### Safe-Operating-Area Specification

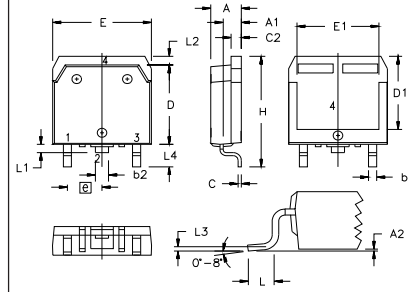
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 1700\text{V}, I_D = 120\text{mA}, T_C = 75^\circ\text{C}, T_p = 5\text{s}$	204		W

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{SD}$	$I_F = 2\text{A}, V_{GS} = -10\text{V}$ , Note 1		0.75	1.30 V
$t_{rr}$	$I_F = 2\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = -10\text{V}$		2.8	$\mu\text{s}$
$I_{RM}$			45.0	A
$Q_{RM}$			63.0	$\mu\text{C}$

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

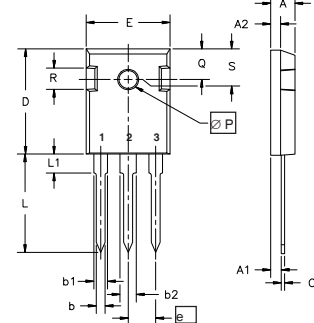
### TO-268 Outline



Terminals: 1 - Gate, 2, 4 - Drain  
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

### TO-247 Outline



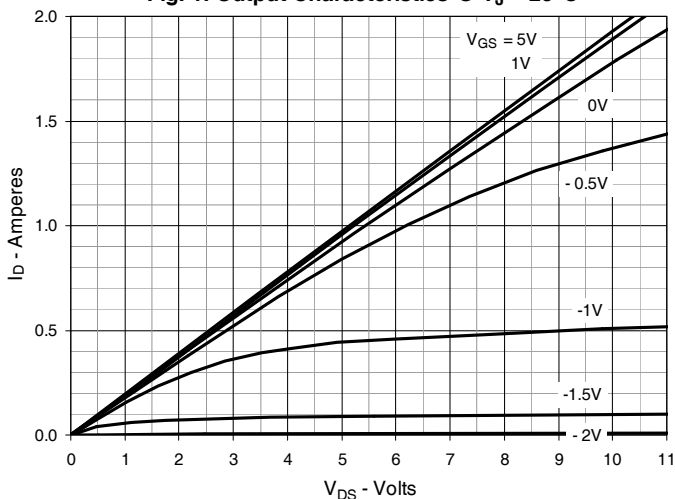
Terminals: 1 - Gate, 2 - Drain  
3 - Source

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

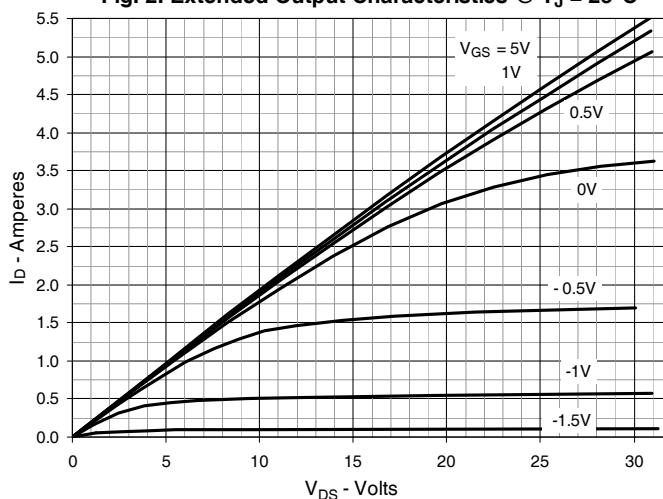
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

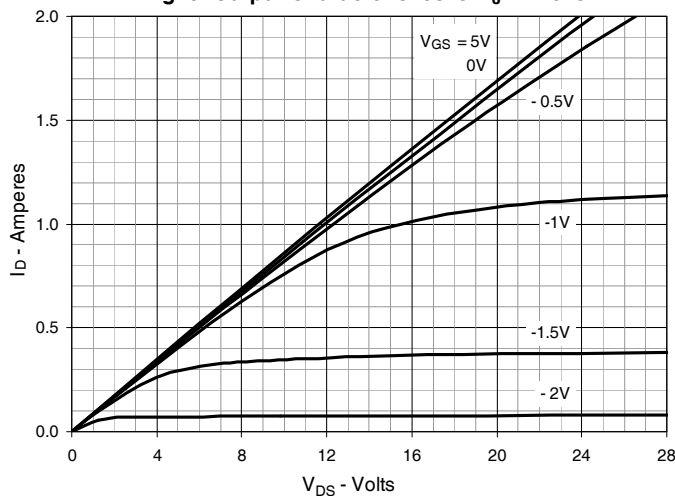
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



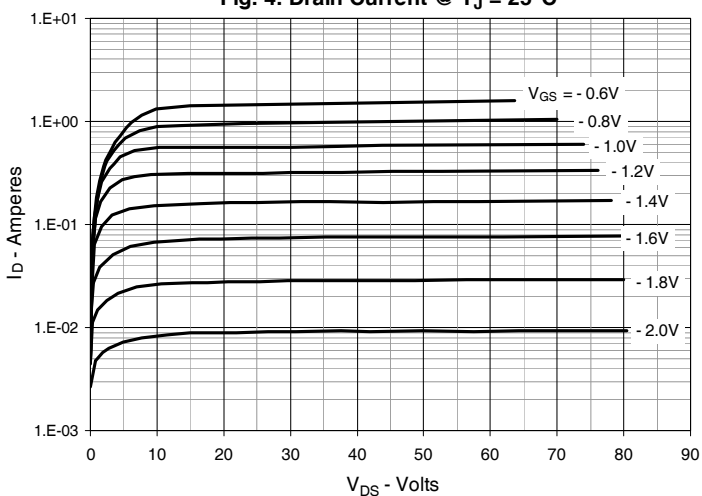
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



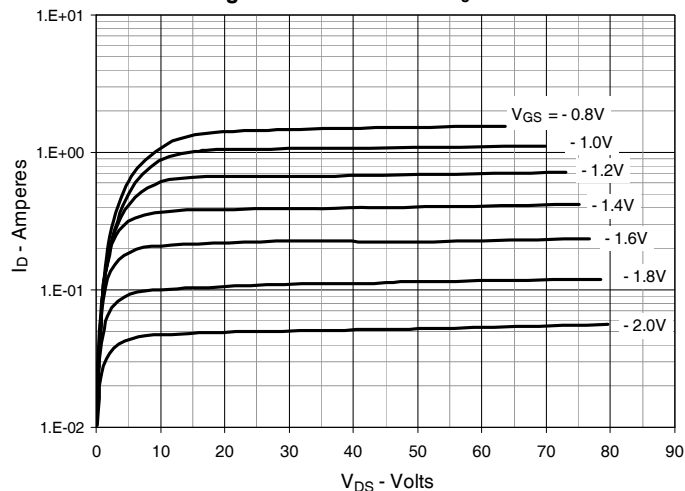
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



**Fig. 4. Drain Current @  $T_J = 25^\circ\text{C}$**



**Fig. 5. Drain Current @  $T_J = 100^\circ\text{C}$**



**Fig. 6. Dynamic Resistance vs. Gate Voltage**

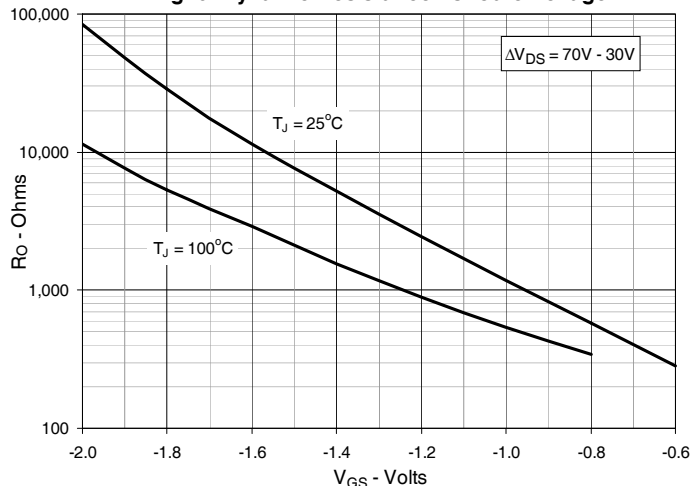


Fig. 7. Dynamic Resistance vs. Gate Voltage

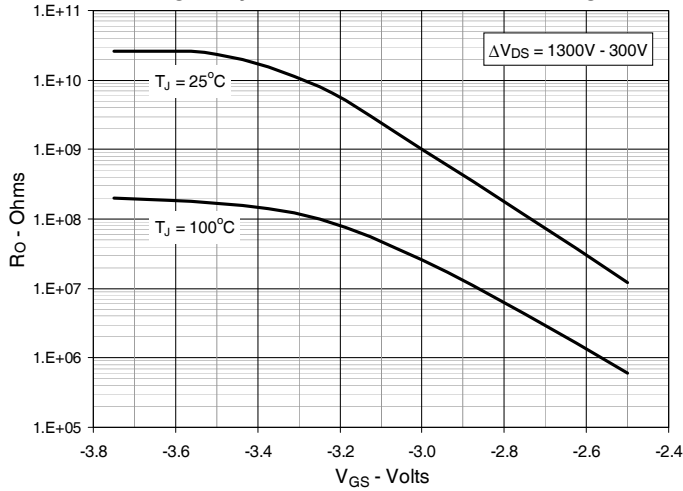


Fig. 8. Normalized  $R_{DS(on)}$  vs. Junction Temperature

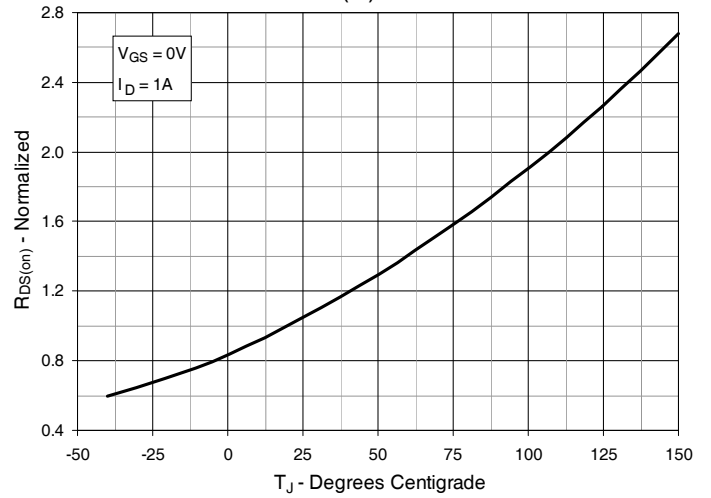


Fig. 9.  $R_{DS(on)}$  Normalized to  $I_D = 1\text{A}$  Value vs. Drain Current

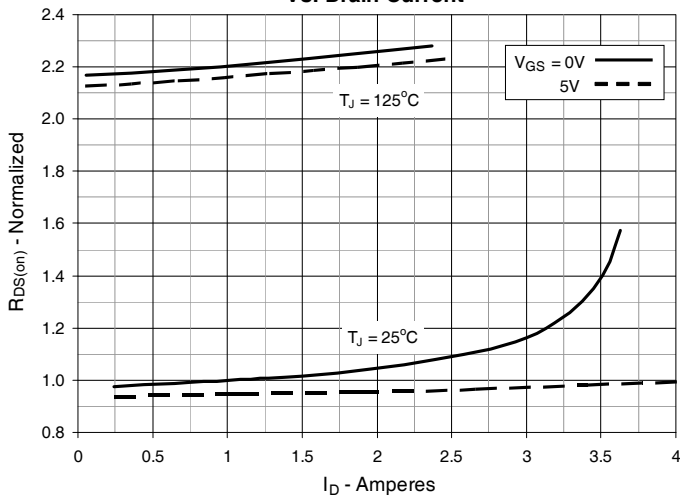


Fig. 10. Input Admittance

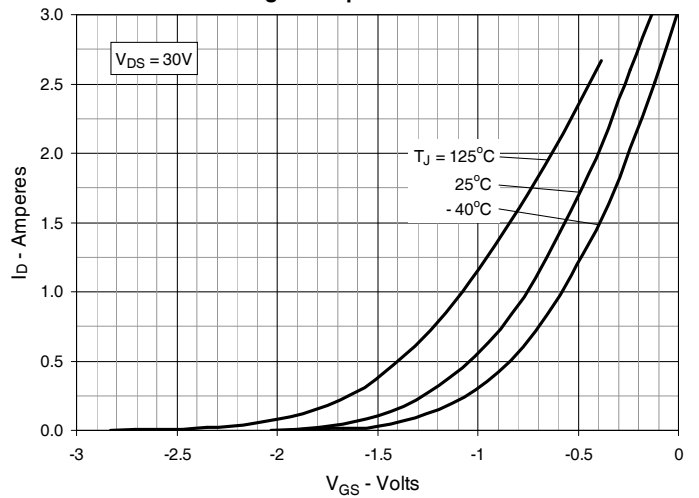


Fig. 11. Transconductance

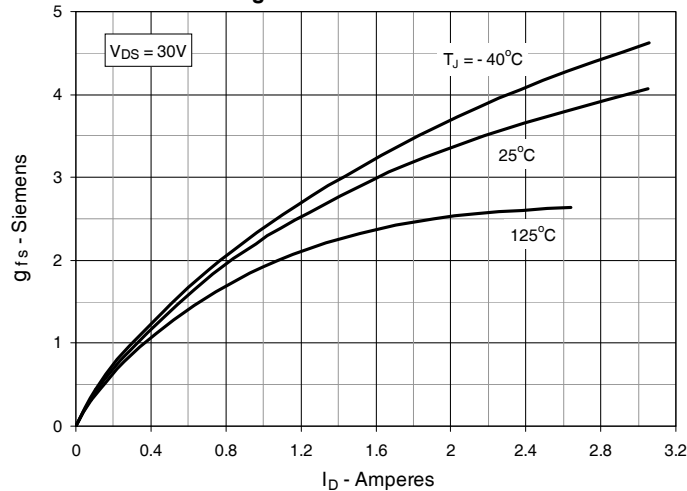
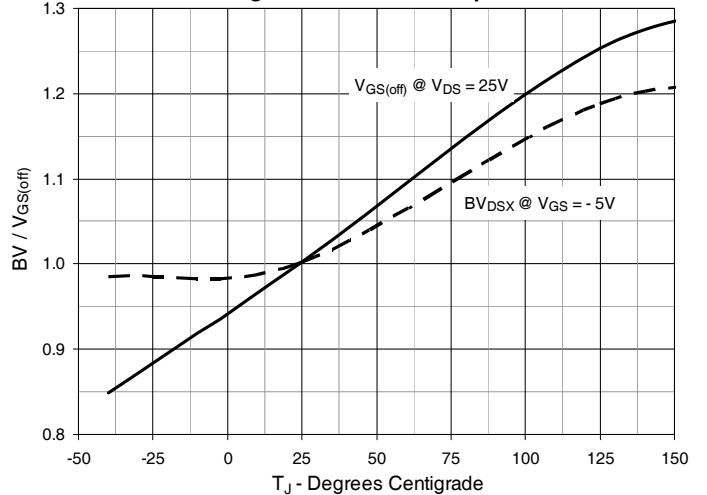
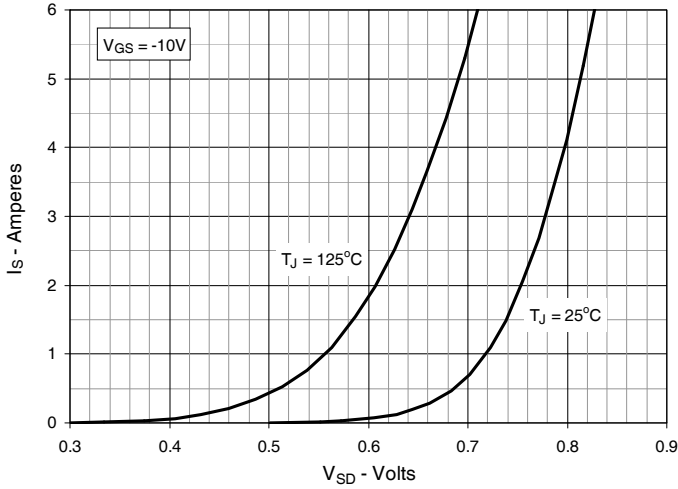


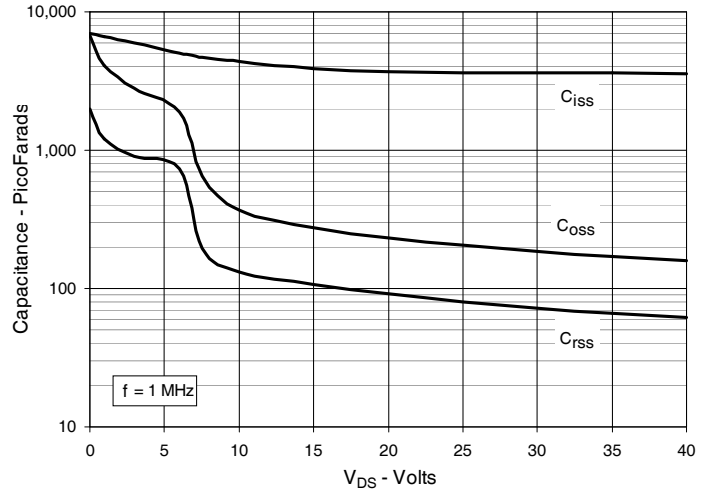
Fig. 12. Normalized Breakdown and Threshold Voltages vs. Junction Temperature



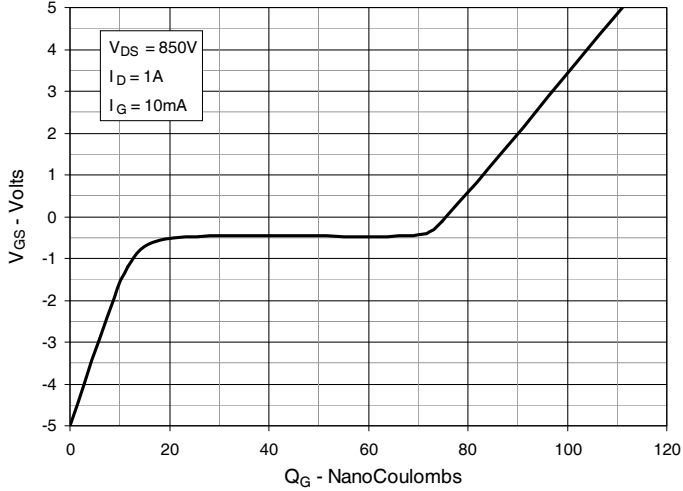
**Fig. 13. Forward Voltage Drop of Intrinsic Diode**



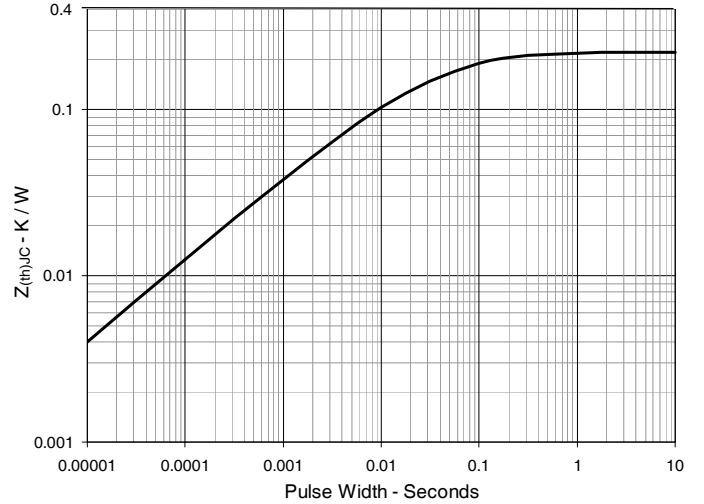
**Fig. 14. Capacitance**



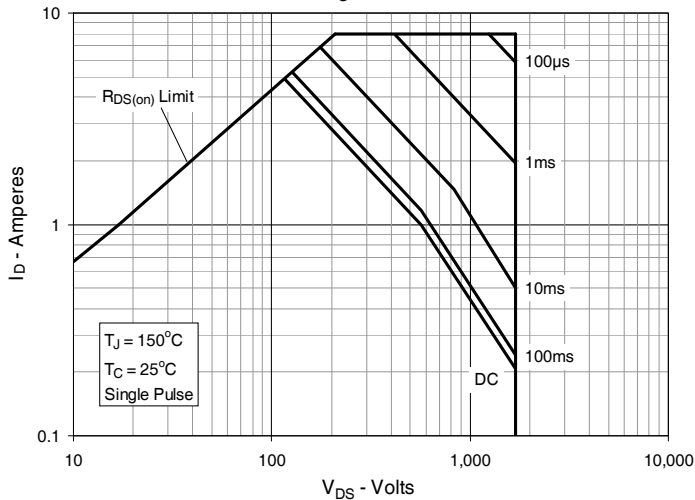
**Fig. 15. Gate Charge**



**Fig. 16. Maximum Transient Thermal Impedance**



**Fig. 17. Forward-Bias Safe Operating Area @  $T_C = 25^\circ\text{C}$**



**Fig. 18. Forward-Bias Safe Operating Area @  $T_C = 75^\circ\text{C}$**

